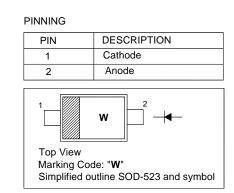
SILICON SCHOTTKY BARRIER DIODE

Features

- Low reverse current, low capacitance
- Ultra small flat package is suitable for surface mount design



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	25	V
Forward Current	I _F	50	mA
Non-Repetitive Peak Forward Surge Current	I _{FSM}	200	mA
Junction Temperature Range	Tj	125	°C
Storage Temperature Range	Ts	- 55 to + 125	°C

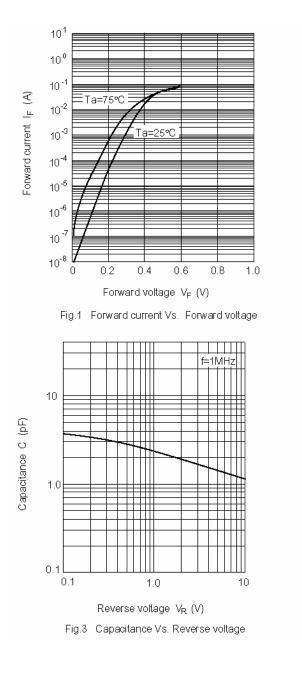
Characteristics at T_a = 25 °C

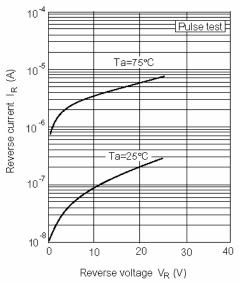
Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 1 mA at I _F = 5 mA	V _F	0.33 0.38	V
Reverse Current at $V_R = 20 V$	I _R	0.45	μΑ
Capacitance at $V_R = 1 V$, f = 1 MHz	С	2.8	pF



















PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

ALL ROUND ∢ H_E D -(A) q ш С V D Е UNIT H_{E} А bp Ζ 0.70 0.60 0.4 0.135 1.25 0.85 1.7 0.1 5° mm 0.3 0.127 1.15 0.75 1.5







Dated : 23/11/2006

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